2SC2768

FUJI POWER TRANSISTOR

TRIPLE DIFFUSED PLANER TYPE
HIGH SPEED SWITCHING

■ Features

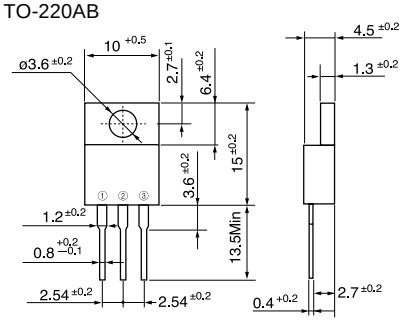
- High speed switching
- High reliability

■ Applications

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

■ Outline Drawings

TO-220AB



1 : Base
2 : Collector
3 : Emitter

JEDEC	TO-220AB
EIAJ	SC-46

■ Maximum ratings and characteristics

● Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Collector-Base voltage	V_{CBO}	250	V
Collector-Emitter voltage	V_{CEO}	200	V
Collector-Emitter voltage	$V_{CEO(SUS)}$	200	V
Emitter-Base voltage	V_{EBO}	7	V
Collector current	I_C	6	A
Base current	I_B	1.5	A
Collector power disspation	P_C	40	W
Operating junction temperature	T_j	+150	℃
Storage temperature	T_{stg}	-55 to +150	℃

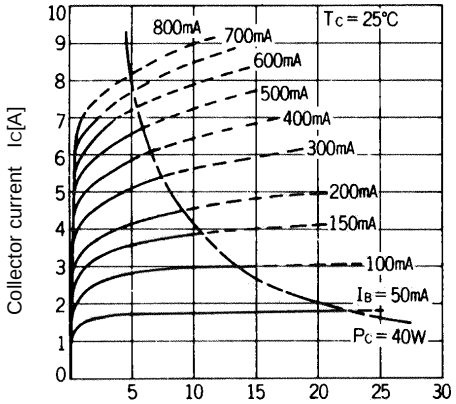
● Electrical characteristics (T_c =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Base voltage	V_{CBO}	I_{CBO} = 0.1mA	250			V
Collector-Emitter voltage	V_{CEO}	I_{CEO} = 10mA	200			V
Collector-Emitter voltage	$V_{CEO(SUS)}$	I_C = 1A	200	-		V
Emitter-Base voltage	V_{EBO}	I_{EBO} = 0.1mA	7	-		V
Collector-Base leakage current	I_{CBO}	V_{CBO} = 250V		-	0.1	mA
Emitter-Base leakage current	I_{EBO}	V_{EBO} = 7V		-	0.1	mA
D.C. current gain	h_{FE}	I_C = 1A, V_{CE} = 5V	20			
Collector-Emitter saturation voltage	$V_{CE(Sat)}$	I_C = 2A, I_B = 0.8A			0.5	V
Base-Emitter saturation voltage	$V_{BE(Sat)}$				1.2	V
*1	t_{on}	I_C = 4A, I_{B1} = 0.4A			1.0	µs
Switching time	t_{stg}	I_{B2} = -0.4A, R_L = 20 ohn			2.0	µs
	t_f	Pw = 20µs Duty=<2%			1.0	µs

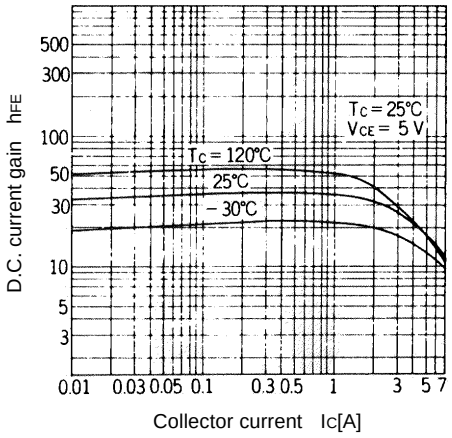
● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(j-c)}$	Junction to case			3.0	°C/W

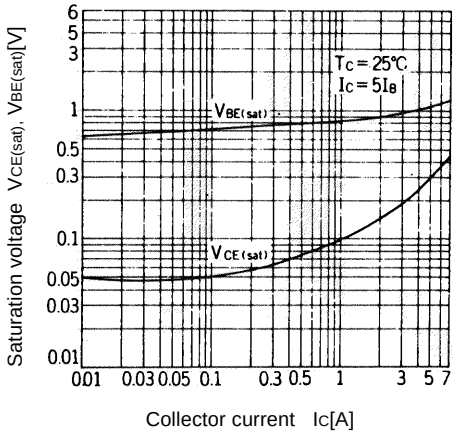
Characteristics



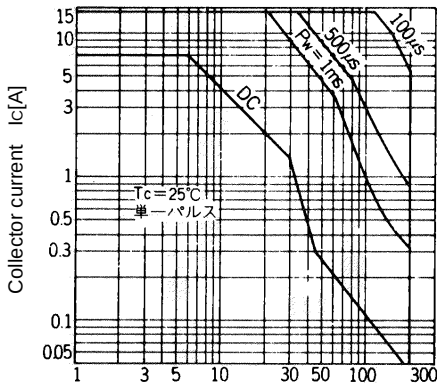
Collector Output Characteristics



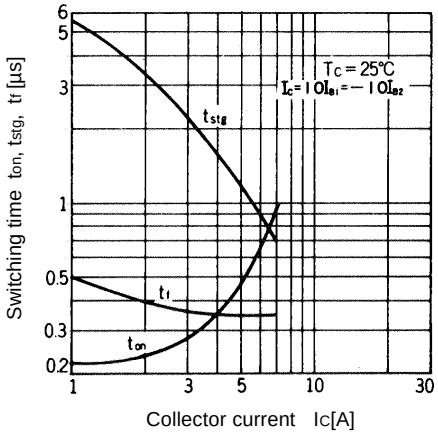
DC Current Gain



Base and Collector Saturation Voltage



Safe Operating Area



Switching Time

***1 Switching Time Test Circuit**